

Nupur Bhargava

List of Publications by Year in descending order

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14
papers

353
citations

1040056

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1125743

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all docs

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docs citations

14
times ranked

437
citing authors

#	ARTICLE	IF	CITATIONS
1	Abrupt SiGe-to-Si interface: influence of chemical vapor deposition processes and characterization by different metrology techniques. <i>Semiconductor Science and Technology</i> , 2018, 33, 104003.	2.0	2
2	Thermal Stability of Annealed Germanium-Tin Alloys Grown by Molecular Beam Epitaxy. <i>Journal of Electronic Materials</i> , 2017, 46, 1620-1627.	2.2	5
3	Fundamentals of Ge _{1-x} Sn _x and Si _y Ge _{1-x-y} Sn _x RPCVD epitaxy. <i>Materials Science in Semiconductor Processing</i> , 2017, 70, 38-43.	4.0	36
4	As doping of Si _{1-x} Ge _x Sn epitaxial semiconductor materials on a commercial CVD reactor. <i>Semiconductor Science and Technology</i> , 2017, 32, 094003.	2.0	6
5	Strain engineering in epitaxial Ge _{1-x} Sn _x : a path towards low-defect and high Sn-content layers. <i>Semiconductor Science and Technology</i> , 2017, 32, 124006.	2.0	35
6	Theoretical study of the effects of strain balancing on the bandgap of dilute nitride InGaSbN/InAs superlattices on GaSb substrates. <i>Infrared Physics and Technology</i> , 2015, 69, 211-217.	2.9	1
7	Infrared photoresponse of GeSn/n-Ge heterojunctions grown by molecular beam epitaxy. <i>Optics Express</i> , 2014, 22, 11029.	3.4	23
8	Structural Properties of Boron-Doped Germanium-Tin Alloys Grown by Molecular Beam Epitaxy. <i>Journal of Electronic Materials</i> , 2014, 43, 931-937.	2.2	11
9	Current-Voltage Characteristics of GeSn/Ge Heterojunction Diodes Grown by Molecular Beam Epitaxy. <i>IEEE Electron Device Letters</i> , 2013, 34, 1217-1219.	3.9	15
10	Photoconductivity of germanium tin alloys grown by molecular beam epitaxy. <i>Applied Physics Letters</i> , 2013, 102, .	3.3	34
11	Infrared electroluminescence from GeSn heterojunction diodes grown by molecular beam epitaxy. <i>Applied Physics Letters</i> , 2013, 102, .	3.3	86
12	Lattice constant and substitutional composition of GeSn alloys grown by molecular beam epitaxy. <i>Applied Physics Letters</i> , 2013, 103, .	3.3	87
13	The properties of germanium-tin alloys for infrared device applications. , 2011, , .		1
14	Magnetic tunneling junction based magnetic field sensors: Role of shape anisotropy versus free layer thickness. <i>Journal of Applied Physics</i> , 2011, 109, .	2.5	11